

<b>Notice of References Cited</b>	Application/Control No. 10/006,704	Applicant(s)/Patent Under Reexamination TRAPP, SHANE J.	
	Examiner Lynette T. Umez-Eronini	Art Unit 1765	Page 1 of 1

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	J	US-			
	K	US-			
	L	US-			
	M	US-			

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	N	JP 54054578A	04-1979	Japan	Yamagishi et al.	H01L 21/302
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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